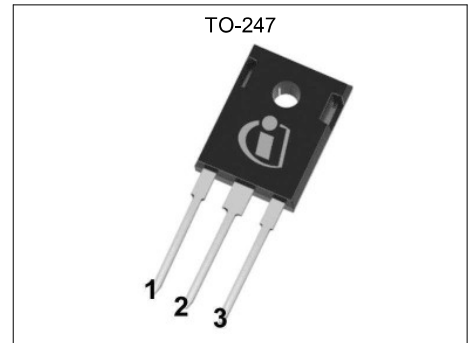


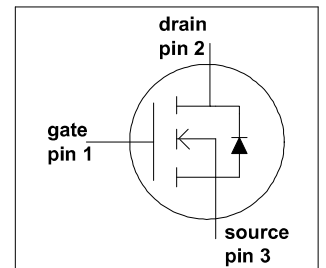
1 Description

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. 650V CoolMOS™ CFD2 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The resulting devices provide all benefits of a fast switching SJ MOSFET while offering an extremely fast and robust body diode. This combination of extremely low switching, commutation and conduction losses together with highest robustness make especially resonant switching applications more reliable, more efficient, lighter and cooler.



Features

- Ultra-fast body diode
- Very high commutation ruggedness
- Extremely low losses due to very low FOM $R_{ds(on)} \cdot Q_g$ and E_{oss}
- Easy to use/drive
- Pb-free plating, Halogen free mold compound
- Qualified for industrial grade applications according to JEDEC (J-STD20 and JESD22)



Applications

650V CoolMOS™ CFD2 is especially suitable for resonant switching PWM stages for e.g. PC Silverbox, LCD TV, Lighting, Server, Telecom and Solar.

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.



Table 1 Key Performance Parameters

| Parameter | Value | Unit |
|-----------------------|-------|------------|
| $V_{DS} @ T_{j \max}$ | 700 | V |
| $R_{DS(on),max}$ | 0.041 | Ω |
| Q_g,typ | 300 | nC |
| $I_D,pulse$ | 255 | A |
| $E_{oss} @ 400V$ | 22.5 | μJ |
| Body diode di/dt | 900 | A/ μs |
| Q_{rr} | 1.9 | μC |
| t_{rr} | 250 | ns |
| I_{rrm} | 15 | A |

| Type / Ordering Code | Package | Marking | Related Links |
|----------------------|-----------|---------|----------------|
| IPW65R041CFD | PG-TO 247 | 65F6041 | see Appendix A |



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2 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|---|----------------|--------|------|-------|------------------|--|
| | | Min. | Typ. | Max. | | |
| Continuous drain current ¹⁾ | I_D | | | 68.5 | A | $T_C = 25^\circ\text{C}$ |
| | | | | 43.3 | | $T_C = 100^\circ\text{C}$ |
| Pulsed drain current ²⁾ | $I_{D,pulse}$ | | | 255 | A | $T_C = 25^\circ\text{C}$ |
| Avalanche energy, single pulse | E_{AS} | | | 2185 | mJ | $I_b = 13.7\text{A}$, $V_{DD} = 50\text{V}$ |
| Avalanche energy, repetitive | E_{AR} | | | 3.31 | mJ | $I_b = 13.7\text{A}$, $V_{DD} = 50\text{V}$ |
| Avalanche current, repetitive | I_{AR} | | | 13.7 | A | |
| MOSFET dv/dt ruggedness | dv/dt | | | 50 | V/ns | $V_{DS} = 0 \dots 400\text{V}$ |
| Gate source voltage | V_{GS} | -20 | | 20 | V | static |
| | | -30 | | 30 | | AC ($f > 1\text{ Hz}$) |
| Power dissipation (non FullPAK) TO-247 | P_{Tot} | | | 500.0 | W | $T_C = 25^\circ\text{C}$ |
| Operating and storage temperature | T_j, T_{stg} | -55 | | 150 | $^\circ\text{C}$ | |
| Mounting torque (non FullPAK) TO-247 | | | | 60 | Ncm | M3 and M3.5 screws |
| Continuous diode forward current | I_S | | | 68.5 | A | $T_C = 25^\circ\text{C}$ |
| Diode pulse current | $I_{S,pulse}$ | | | 255 | A | $T_C = 25^\circ\text{C}$ |
| Reverse diode dv/dt ³⁾ | dv/dt | | | 50 | V/ns | $V_{DS} = 0 \dots 400\text{V}$, $I_{SD} \leq I_b$, $T_j = 25^\circ\text{C}$ |
| Maximum diode commutation speed | di_f/dt | | | 900 | A/ μs | |

¹⁾ Limited by $T_{j\text{ max}}$.

²⁾ Pulse width t_p limited by $T_{j\text{ max}}$

³⁾ $V_{peak} < V_{(BR)DSS}$, $T_j < T_{j\text{ max}}$, identical low and high side switch with same R_g

3 Thermal characteristics

Table 3 Thermal characteristics TO-247

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|------------|--------|------|------|------|--------------------------------------|
| | | Min. | Typ. | Max. | | |
| Thermal resistance, junction - case | R_{thJC} | | | 0.25 | °C/W | |
| Thermal resistance, junction - ambient | R_{thJA} | | | 62 | °C/W | leaded |
| Soldering temperature, wavesoldering only allowed at leads | T_{sold} | | | 260 | °C | 1.6 mm (0.063 in.) from case for 10s |

4 Electrical characteristics

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 4 Static characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|----------------------------------|---------------|--------|-------|-------|----------|---|
| | | Min. | Typ. | Max. | | |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | 650 | | | V | $V_{GS} = 0V, I_D = 1mA$ |
| Gate threshold voltage | $V_{GS(th)}$ | 3.5 | 4 | 4.5 | V | $V_{DS} = V_{GS}, I_D = 3.3mA$ |
| Zero gate voltage drain current | I_{DSS} | | | 3.5 | μA | $V_{DS} = 650V, V_{GS} = 0V, T_j = 25^\circ C$ |
| | | | 1000 | | | $V_{DS} = 650V, V_{GS} = 0V, T_j = 150^\circ C$ |
| Gate-source leakage current | I_{GSS} | | | 100 | nA | $V_{GS} = 20V, V_{DS} = 0V$ |
| Drain-source on-state resistance | $R_{DS(on)}$ | | 0.037 | 0.041 | Ω | $V_{GS} = 10V, I_D = 33.1A, T_j = 25^\circ C$ |
| | | | 0.096 | | | $V_{GS} = 10V, I_D = 33.1A, T_j = 150^\circ C$ |
| Gate resistance | R_G | | 0.7 | | Ω | $f = 1MHz, \text{open drain}$ |

Table 5 Dynamic characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|--------------|--------|------|------|------|---|
| | | Min. | Typ. | Max. | | |
| Input capacitance | C_{iss} | | 8400 | | pF | $V_{GS} = 0V, V_{DS} = 100V, f = 1MHz$ |
| Output capacitance | C_{oss} | | 400 | | pF | |
| Effective output capacitance, energy related ¹⁾ | $C_{o(er)}$ | | 288 | | pF | $V_{GS} = 0V, V_{DS} = 0 \dots 400V$ |
| Effective output capacitance, time related ²⁾ | $C_{o(tr)}$ | | 1485 | | pF | $I_D = \text{constant}, V_{GS} = 0V, V_{DS} = 0 \dots 400V$ |
| Turn-on delay time | $t_{d(on)}$ | | 34 | | ns | $V_{DD} = 400V, V_{GS} = 13V, I_D = 49.6A, R_G = 1.8\Omega$ |
| Rise time | t_r | | 28 | | ns | |
| Turn-off delay time | $t_{d(off)}$ | | 127 | | ns | |
| Fall time | t_f | | 8 | | ns | |

Table 6 Gate charge characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|-----------------------|---------------|--------|------|------|------|--|
| | | Min. | Typ. | Max. | | |
| Gate to source charge | Q_{gs} | | 54 | | nC | $V_{DD} = 480V, I_D = 49.6A, V_{GS} = 0 \text{ to } 10V$ |
| Gate to drain charge | Q_{gd} | | 165 | | nC | |
| Gate charge total | Q_g | | 300 | | nC | |
| Gate plateau voltage | $V_{plateau}$ | | 6.5 | | V | |

¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400V

²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400V

Table 7 Reverse diode characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|-------------------------------|-----------|--------|------|------|---------|---|
| | | Min. | Typ. | Max. | | |
| Diode forward voltage | V_{SD} | | 1 | | V | $V_{GS} = 0V, f = 49.6A, T_j = 25^\circ C$ |
| Reverse recovery time | t_{rr} | | 250 | | ns | $V_R = 400V, f = 49.6A, dI/dt = 100A/\mu s$ |
| Reverse recovery charge | Q_{rr} | | 1.9 | | μC | |
| Peak reverse recovery current | I_{rrm} | | 15 | | A | |

